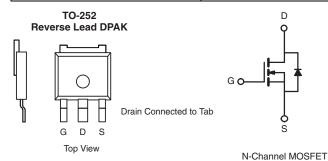


SQR50N06-07L Automotive N-Channel

60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0076			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.009			
I _D (A)	50			
Configuration	Single			



FEATURES

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested
- AEC-Q101 Qualifiedd



ORDERING INFORMATION				
Package	TO-252 Reverse Lead DPAK			
Lead (Pb)-free and Halogen-free	SQR50N06-07L-GE3			

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	otherwise noted	d)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current ^a	T _C = 25 °C	- I _D	50	
	T _C = 125 °C		50	
Continuous Source Current (Diode Conduction) ^a		Is	50	Α
Pulsed Drain Current ^b		I _{DM}	200	
Single Pulse Avalanche Current	1 0.1 ml l	I _{AS}	48	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	115	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	P _D	136	W
	T _C = 125 °C		45	
Operating Junction and Storage Temperatur	e Range	T _J , T _{stq}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.1	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



SQR50N06-07L Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							L
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60		-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}$, $I_{D} = 250 \mu\text{A}$		2.0	2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 60 V	-	-	1.0	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
		V _{GS} = 10 V	I _D = 20 A	-	0.0064	0.0076	
Duein Course On Chata Basistanas		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0130	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0160	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0078	0.0090	
Forward Transconductanceb	9fs	V _{DS}	= 15 V, I _D = 20 A	-	82	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	4455	5570	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	407	510	
Reverse Transfer Capacitance	C _{rss}	1		-	223	280	
Total Gate Charge ^c	Qg			-	80	120	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 50 \text{ A}$	-	11.1	-	nC
Gate-Drain Charge ^c	Q _{gd}	1		-	15.7	-	
Gate Resistance	R_g	f = 1 MHz		1	2	3	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	12	18	
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, \text{ R}_L = 0.6 \Omega$ $I_D \cong 50 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	13	20	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	42	63	
Fall Time ^c	t _f			-	7	11	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	200	Α
Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		-	0.85	1.5	V

Notes

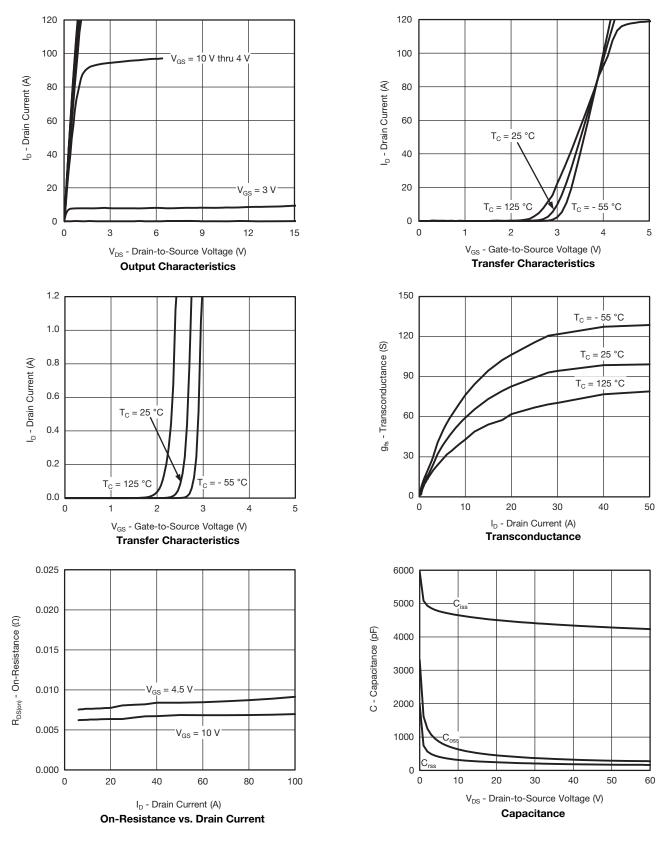
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



Automotive N-Channel 60 V (D-S) 175 °C MOSFET

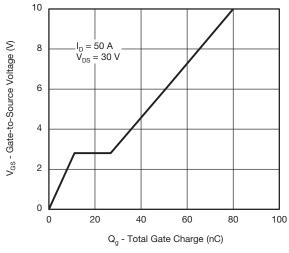
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



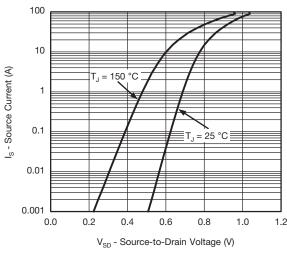


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

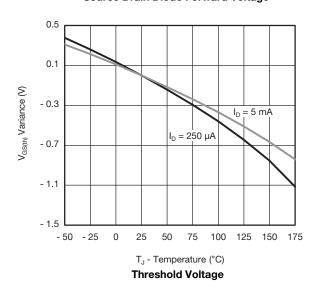
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Gate Charge

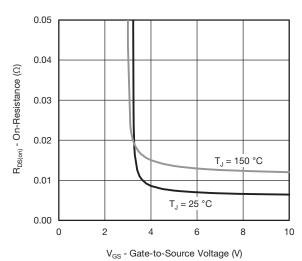


Source Drain Diode Forward Voltage

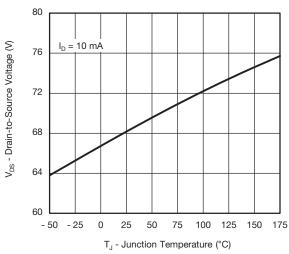


I_D = 20 A 2.0 R_{DS(on)} - On-Resistance (Normalized) 1.7 1.4 1.1 0.8 0.5 - 25 0 75 100 125 150 175 - 50 25 50 T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature



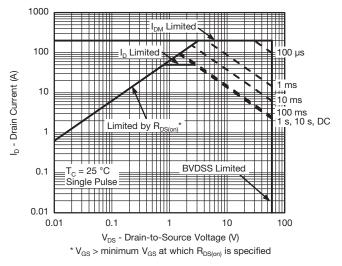
On-Resistance vs. Gate-to-Source Voltage



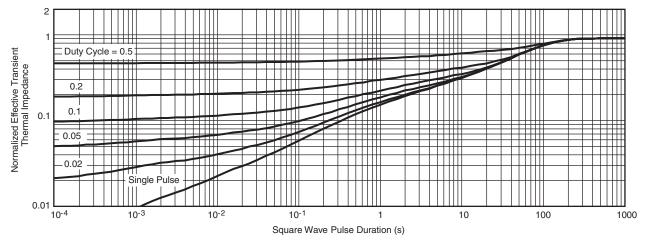
Drain Source Breakdown vs. Junction Temperature

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



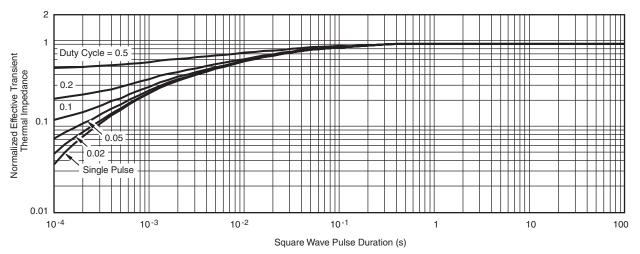
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

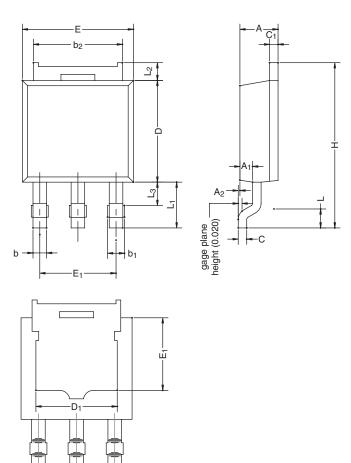
- · The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



Automotive N-Channel 60 V (D-S) 175 °C MOSFET

TO-252 REVERSE LEAD CASE OUTLINE



	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.23	2.33	0.088	0.092	
A ₁	0.64	0.89	0.025	0.035	
A ₂	0.03	0.23	0.001	0.009	
b	0.71	0.88	0.028	0.035	
b ₁	0.76	1.14	0.030	0.045	
b ₂	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C ₁	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D ₁	4.49	5.00	0.177	0.197	
E	6.48	6.73	0.255	0.265	
E ₁	4.32	-	0.170	-	
е	2.28 BSC		0.090	BSC	
e ₁	4.57 BSC		0.180	BSC	
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L ₁	2.74 BSC		0.108	BSC	
L ₂	0.89	1.27	0.035	0.050	
L ₃	1.15	1.52	0.040	0.060	
ECN: T-08706-Rev. B, 29-Sep-08 DWG: 5894					

Note

Dimension L₃ for reference only.



SQR50N06-07L Automotive N-Channel 60 V (D-S) 175 °C MOSFET

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